Product data sheet

1. General description

P-channel enhancement mode Field-Effect Transistor (FET) in a small SOT23 (TO-236AB) Surface-Mounted Device (SMD) plastic package using Trench MOSFET technology.

2. Features and benefits

- Low threshold voltage
- Extended temperature range T_i = 175 °C
- Trench MOSFET technology
- Very fast switching
- AEC-Q101 qualified

3. Applications

- Relay driver
- · High-speed line driver
- · High-side load switch
- · Switching circuits

4. Quick reference data

Table 1. Quick reference data

Symbol	Parameter	Conditions		Min	Тур	Max	Unit
V _{DS}	drain-source voltage	T _j = 25 °C		-	-	-20	V
V_{GS}	gate-source voltage			-12	-	12	V
I _D	drain current	V _{GS} = -4.5 V; T _{amb} = 25 °C	[1]	-	-	-4	Α
Static charac	teristics		·				
R _{DSon}	drain-source on-state resistance	V_{GS} = -4.5 V; I_D = -4 A; T_j = 25 °C		-	43	55	mΩ

[1] Device mounted on an FR4 Printed-Circuit Board (PCB), single-sided copper, tin-plated and mounting pad for drain 6 cm².



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5. Pinning information

Table 2. Pinning information

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	G	gate	3	D I
2	S	source		
3	D	drain		G LITTLE
			1 2	S 017aaa257
			SOT23	

6. Ordering information

Table 3. Ordering information

Type number	Package					
	Name	Description	Version			
PMV48XPA2	SOT23	plastic, surface-mounted package; 3 terminals; 1.9 mm pitch; 2.9 mm x 1.3 mm x 1 mm body	SOT23			

7. Marking

Table 4. Marking codes

Type number	Marking code[1]
PMV48XPA2	%HG

[1] % = placeholder for manufacturing site code

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8. Limiting values

Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions		Min	Max	Unit
V _{DS}	drain-source voltage	T _j = 25 °C		-	-20	V
V _{GS}	gate-source voltage			-12	12	V
I _D	drain current	V _{GS} = -4.5 V; T _{amb} = 25 °C	[1]	-	-4	Α
		V _{GS} = -4.5 V; T _{amb} = 100 °C	[1]	-	-2.6	Α
I _{DM}	peak drain current	T_{amb} = 25 °C; single pulse; $t_p \le 10 \mu s$		-	-16	Α
P _{tot}	total power dissipation	T _{amb} = 25 °C	[2]	-	610	mW
			[1]	-	1.4	W
		T _{sp} = 25 °C		-	8.3	W
Tj	junction temperature			-55	175	°C
T _{amb}	ambient temperature			-55	175	°C
T _{stg}	storage temperature			-65	175	°C
Source-drain	diode					
Is	source current	T _{amb} = 25 °C	[1]	-	-1.5	Α
ESD maximu	m rating					
V _{ESD}	electrostatic discharge voltage	НВМ	[3]	-	400	V
Avalanche ru	ggedness					
E _{DS(AL)S}	non-repetitive drain- source avalanche energy	$T_{j(init)}$ = 25 °C; I_D = -1 A; DUT in avalanche (unclamped)		-	10	mJ

- [1] Device mounted on an FR4 Printed-Circuit Board (PCB), single-sided copper, tin-plated and mounting pad for drain 2 .
- [2] Device mounted on an FR4 Printed-Circuit Board (PCB), single-sided copper, tin-plated and standard footprint.
- [3] Measured between all pins.

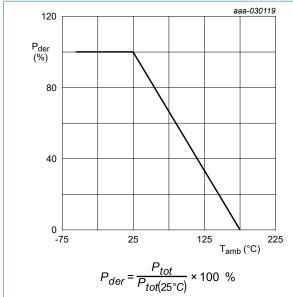


Fig. 1. Normalized total power dissipation as a function of ambient temperature

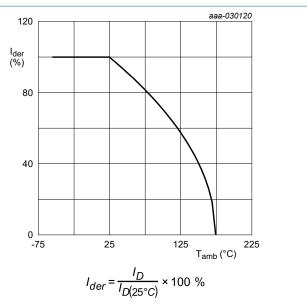


Fig. 2. Normalized continuous drain current as a function of ambient temperature

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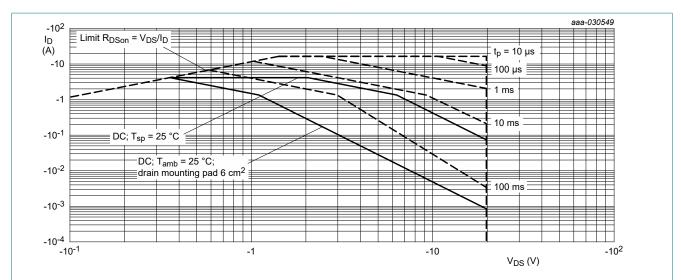


Fig. 3. Safe operating area; junction to ambient; continuous and peak drain currents as a function of drain-source voltage

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9. Thermal characteristics

Table 6. Thermal characteristics

Symbol	Parameter	Conditions		Min	Тур	Max	Unit
R _{th(j-a)}	thermal resistance from	in free air	[1]	-	208	245	K/W
j	junction to ambient		[2]	-	88	104	K/W
R _{th(j-sp)}	thermal resistance from junction to solder point			-	13	18	K/W

- [1] Device mounted on an FR4 PCB, single-sided copper, tin-plated and standard footprint.
- [2] Device mounted on an FR4 PCB, single-sided copper, tin-plated and mounting pad for drain 6 cm².

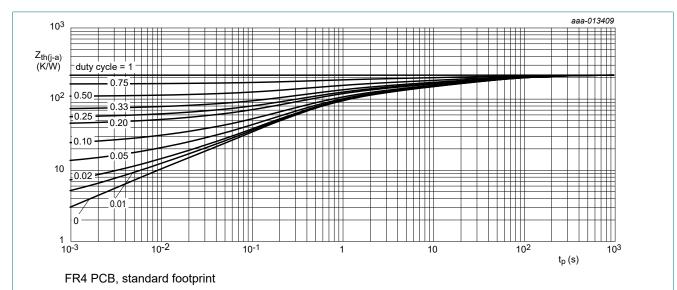


Fig. 4. Transient thermal impedance from junction to ambient as a function of pulse duration; typical values

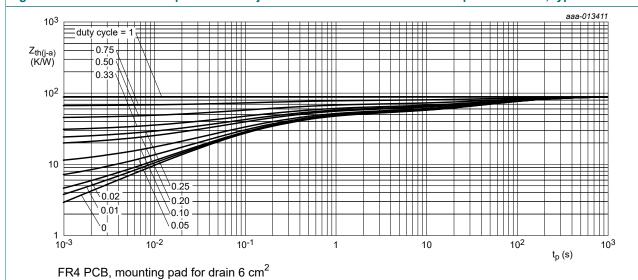


Fig. 5. Transient thermal impedance from junction to ambient as a function of pulse duration; typical values

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10. Characteristics

Table 7. Characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Static chara	acteristics					
V _{(BR)DSS}	drain-source breakdown voltage	I_D = -250 μ A; V_{GS} = 0 V; T_j = 25 °C	-20	-	-	V
V_{GSth}	gate-source threshold voltage	$I_D = -250 \ \mu A; \ V_{DS} = V_{GS}; \ T_j = 25 \ ^{\circ}C$	-0.6	-0.95	-1.3	V
I _{DSS}	drain leakage current	V _{DS} = -20 V; V _{GS} = 0 V; T _j = 25 °C	-	-	-1	μΑ
I _{GSS}	gate leakage current	V _{GS} = -12 V; V _{DS} = 0 V; T _j = 25 °C	-	-	-100	nA
		V _{GS} = 12 V; V _{DS} = 0 V; T _j = 25 °C	-	-	100	nA
R _{DSon}	drain-source on-state	$V_{GS} = -8 \text{ V}; I_D = -4 \text{ A}; T_j = 25 ^{\circ}\text{C}$	-	37	49	mΩ
	resistance	V _{GS} = -8 V; I _D = -4 A; T _j = 175 °C	-	59	78	mΩ
		$V_{GS} = -4.5 \text{ V}; I_D = -4 \text{ A}; T_j = 25 \text{ °C}$	-	43	55	mΩ
		V _{GS} = -2.5 V; I _D = -1 A	-	65	90	mΩ
9 _{fs}	forward transconductance	V_{DS} = -10 V; I_{D} = -4.2 A; T_{j} = 25 °C	-	54	-	S
R_G	gate resistance	f = 1 MHz	-	7	-	Ω
Dynamic ch	naracteristics		'			
Q _{G(tot)}	total gate charge	V _{DS} = -10 V; I _D = -4.2 A; V _{GS} = -4.5 V;	-	7	10	nC
Q _{GS}	gate-source charge	T _j = 25 °C	-	1.3	-	nC
Q_{GD}	gate-drain charge		-	2.3	-	nC
C _{iss}	input capacitance	V _{DS} = -10 V; f = 1 MHz; V _{GS} = 0 V;	-	679	-	pF
C _{oss}	output capacitance	T _j = 25 °C	-	87	-	pF
C _{rss}	reverse transfer capacitance		-	75	-	pF
t _{d(on)}	turn-on delay time	V _{DS} = -10 V; I _D = -4.2 A; V _{GS} = -4.5 V;	-	7	-	ns
t _r	rise time	$R_{G(ext)} = 6 \Omega; T_j = 25 °C$	-	19	-	ns
t _{d(off)}	turn-off delay time	1	-	26	-	ns
t _f	fall time]	-	13	-	ns
Source-drai	in diode		'			
V _{SD}	source-drain voltage	$I_S = -1.5 \text{ A}; V_{GS} = 0 \text{ V}; T_j = 25 ^{\circ}\text{C}$	-	-0.8	-1.2	V
t _{rr}	reverse recovery time	I _S = -1.7 A; dI _S /dt = 100 A/μs;	-	10	-	ns
Q _r	recovered charge	V _{GS} = 0 V; V _{DS} = -10 V; T _j = 25 °C	-	2	-	nC

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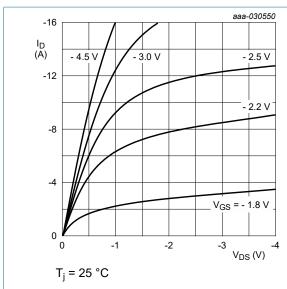


Fig. 6. Output characteristics: drain current as a function of drain-source voltage; typical values

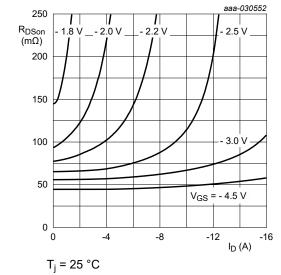


Fig. 8. Drain-source on-state resistance as a function of drain current; typical values

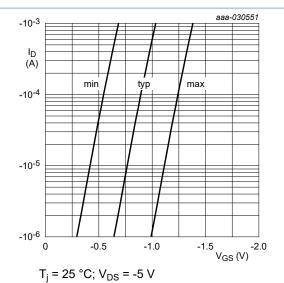


Fig. 7. Subthreshold drain current as a function of

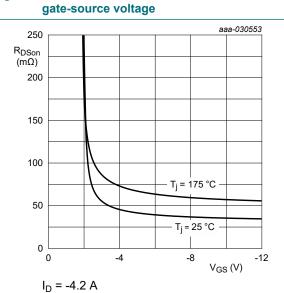


Fig. 9. Drain-source on-state resistance as a function of gate-source voltage; typical values

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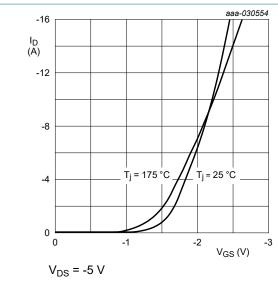


Fig. 10. Transfer characteristics: drain current as a function of gate-source voltage; typical values

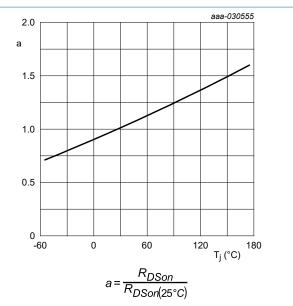


Fig. 11. Normalized drain-source on-state resistance as a function of junction temperature; typical values

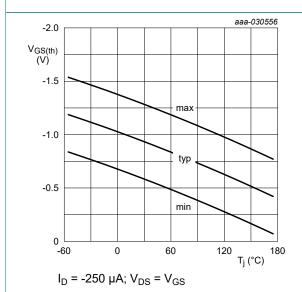
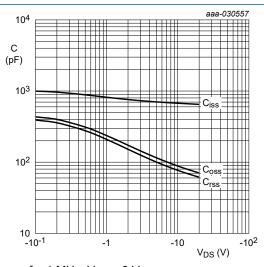


Fig. 12. Gate-source threshold voltage as a function of junction temperature



 $f = 1 \text{ MHz}; V_{GS} = 0 \text{ V}$

Fig. 13. Input, output and reverse transfer capacitances as a function of drain-source voltage; typical values

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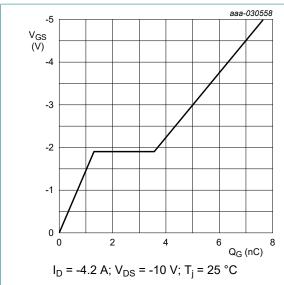


Fig. 14. Gate-source voltage as a function of gate charge; typical values

 $V_{GS} = 0 V$

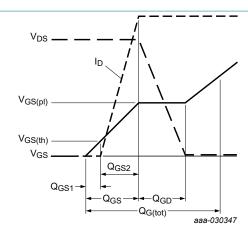


Fig. 15. Gate charge waveform definitions

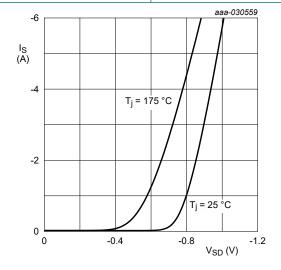
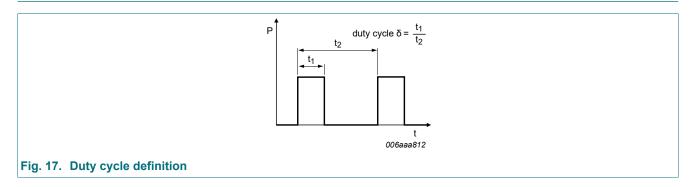


Fig. 16. Source current as a function of source-drain voltage; typical values

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11. Test information



Quality information

This product has been qualified in accordance with the Automotive Electronics Council (AEC) standard *Q101 - Stress test qualification for discrete semiconductors*, and is suitable for use in automotive applications.

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12. Package outline

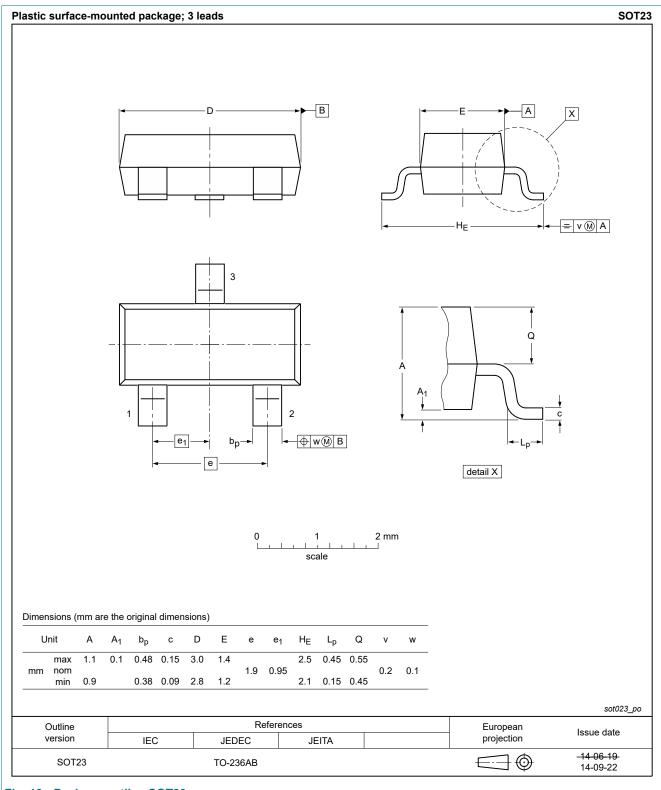
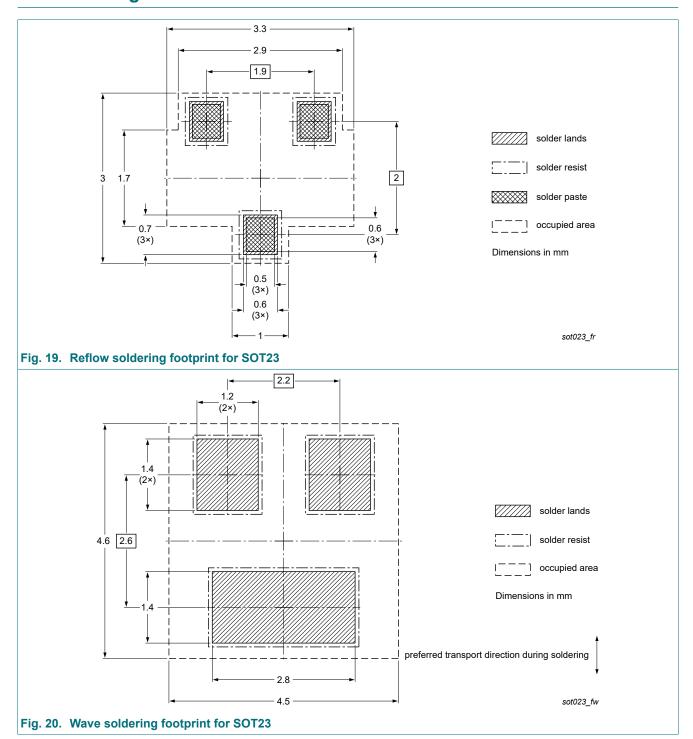


Fig. 18. Package outline SOT23

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13. Soldering



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14. Revision history

Table 8. Revision history

- Laboration in the contract of the contract o								
Data sheet ID	Release date	Data sheet status	Change notice	Supersedes				
PMV48XPA2 v.3	20200428	Product data sheet	-	PMV48XPA2 v.2				
	Characteristics: Condition for "Reverse recovery time" and "Recovered charge" revised							
PMV48XPA2 v.2	20200220	Product data sheet	-	PMV48XPA2 v.1				
PMV48XPA2 v.1	20200107	Product data sheet	-	-				

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15. Legal information

Data sheet status

Document status [1][2]	Product status [3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

- Please consult the most recently issued document before initiating or completing a design.
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PMV48XPA2

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